



N-channel Enhancement Mode Mosfet

CX4515

DESCRIPTION

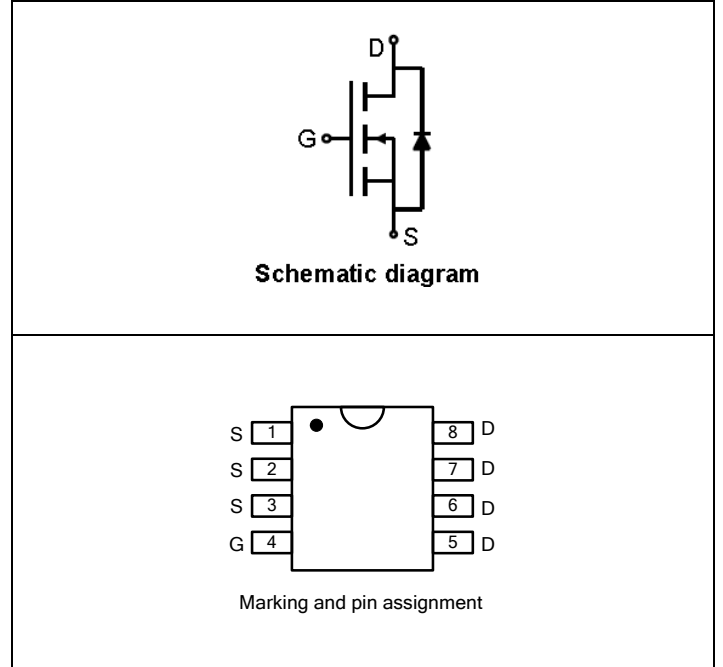
The CX4515 uses advanced trench technology to provide excellent RDS(ON) and low gate charge. This device is suitable for use as a load switch or in PWM applications.

GENERAL FEATURES

- RDS(ON) < 22m Ω @ VGS=4.5V
RDS(ON) < 15m Ω @ VGS=10V
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

Application

- PWM applications
- Load switch
- Power management



ABSOLUTE MAXIMUM RATINGS(T_A=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current @ Continuous(Note 2)	I _D (25°C)	30	A
	I _D (100°C)	20	A
Drain Current @ Current-Pulsed (Note 1)	I _{DM}	112	A
Maximum Power Dissipation (T _A =25°C)	P _D	35	W
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance,Junction-to-Ambient (Note 2)	RθJA	35	°C/W
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